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P-Channel 40 V (D-S) MOSFEET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 40	0.0046 at V _{GS} = - 10 V	- 95 ^d		
- 40	0.0062 at V _{GS} = - 4.5 V	- 82 ^d		

FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested

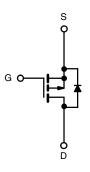


APPLICATIONS

· Load Switch



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	- 40	V			
Gate-Source Voltage	V _{GS}	± 20]			
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	I_	- 95 ^d			
Continuous Drain Current (1) = 173 O)	T _C = 125 °C	- I _D	- 63	A		
Pulsed Drain Current	I _{DM}	- 360	^			
Avalanche Current	I _{AR}	- 88				
Avalanche energy, single pulse ^a	L = 0.1 mH	E _{AS}	75	mJ		
Power Dissination	T _C = 25 °C	P _D	135 ^c	- W		
Power Dissipation	T _A = 25 °C] 'D	6.3 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lumation to Ambionth	t ≤ 10 s	- R _{thJA}	20	30	°C/W	
Junction-to-Ambient ^b	Steady State		40	60		
Junction-to-Case		R _{thJC}	-	1.5		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min. Typ.		Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 40			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 40 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
		V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 150 °C			- 100	1	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 95			Α	
D : 0		V _{GS} = - 10 V, I _D = - 30 A		0.0046	0.0059	-	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 20 A		0.0062	0.0085	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 30 A	30 A 83			S	
Dynamic ^b							
Input Capacitance	C _{iss}			6910			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$		2082		pF	
Reverse Transfer Capacitance	C _{rss}			162		1	
Total Gate Charge ^c	Q_g			139			
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -30 \text{ A}$		40		nC	
Gate-Drain Charge ^c	Q_{gd}			20			
Turn-On Delay Time ^c	t _{d(on)}			25			
Rise Time ^c	t _r	V_{DD} = - 20 V, R_L = 0.6 Ω		30			
Turn-Off Delay Time ^c	t _{d(off)}	$I_{D} = -30 \text{ A}, V_{GEN} = -10 \text{ V}, R_{G} = 6\Omega$		138		ns	
Fall Time ^c	t _f			55			
Source-Drain Diode Ratings and Characteristics $T_C = 25 {}^{\circ}\text{C}^{\text{b}}$							
Continuous Current	I _S				- 95	Α	
Forward Voltage ^a	V_{SD}	I _F = - 1 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Reverse Recovery Time	t _{rr}	I _F = - 10 A, dI/dt = 100 A/μs		59		ns	
Reverse Recovery Charge	Q _{rr}	I _F = - 10 A, dl/dt = 100 A/μs		82		nC	

Notes:

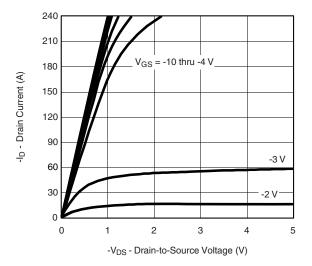
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

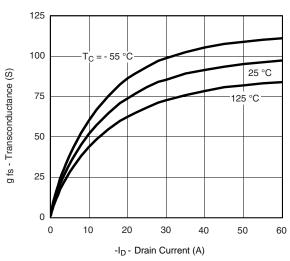
Rev. 1.0 2



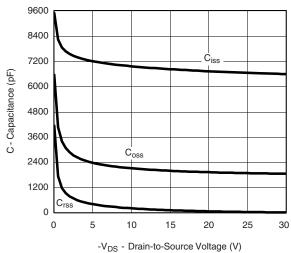
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



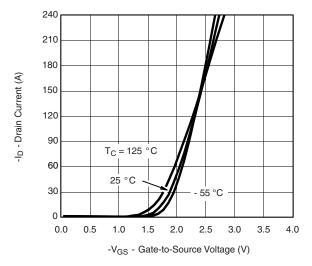
Output Characteristics



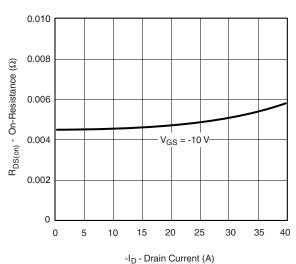
Transconductance



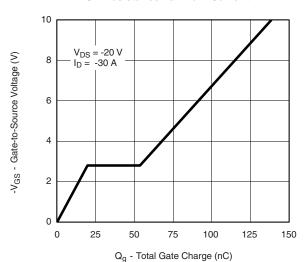
Capacitance



Transfer Characteristics



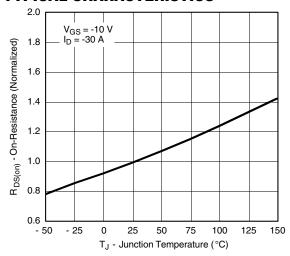
On-Resistance vs. Drain Current



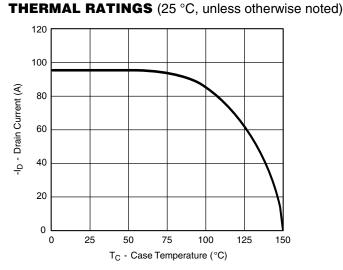
Gate Charge



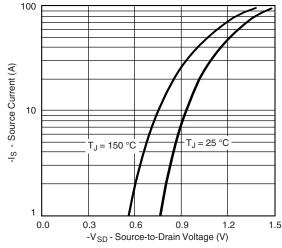
TYPICAL CHARACTERISTICS



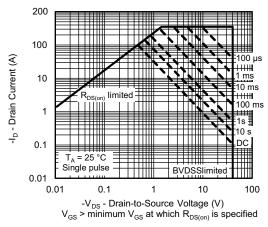
On-Resistance vs. Junction Temperature



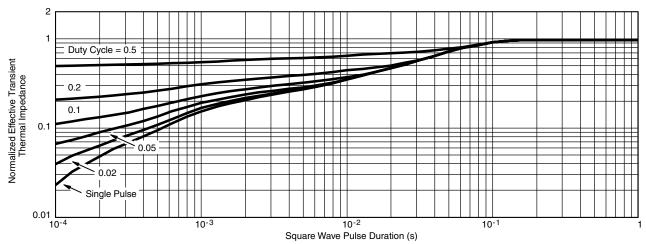
Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



Safe Operating Area, Junction-to-Ambient

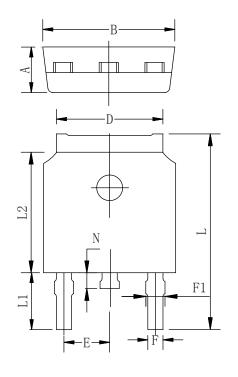


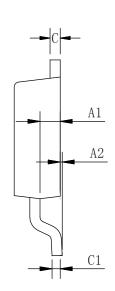
Normalized Thermal Transient Impedance, Junction-to-Case



Din-Tek SEMICONDUCTOR







COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
C	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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